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Kind regards,

Team Nexperia



BC847BS

45 V, 100 mA NPN/NPN general-purpose transistor Rev. 03 — 18 February 2009 Produ

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: BC857BS.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	-	450	



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2. Pinning information

Table 2. Pinning

Table 2.	riiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	D- D- D-	
2	base TR1	<u> </u>	6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym020

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847BS	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
BC847BS	1F*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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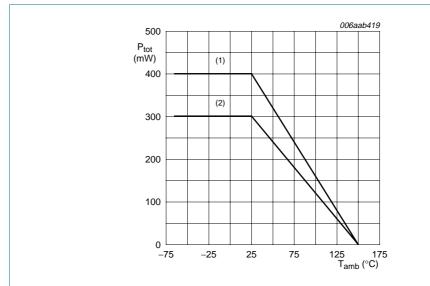
5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	220	mW
			[2] -	250	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	300	mW
			[2] -	400	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, mounting pad for collector 1 cm²
- (2) FR4 PCB, standard footprint

Fig 1. Per device: Power derating curves SOT363 (SC-88)

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6. Thermal characteristics

Table 6. Thermal characteristics

	_					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
· •(i)(j-a)	thermal resistance from junction to ambient	in free air	[1] _	-	568	K/W
			[2] _	-	500	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	230	K/W
Per device						
R _{th(j-a)}	thermal resistance from	in free air	[1] -	-	416	K/W
	junction to ambient		[2] _	-	313	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

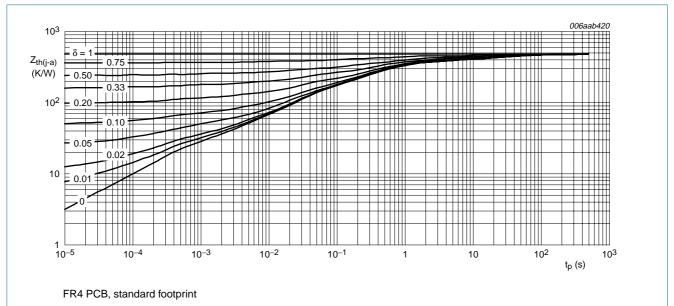
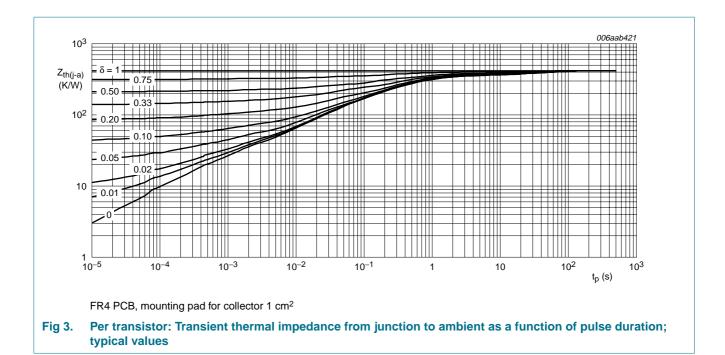


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

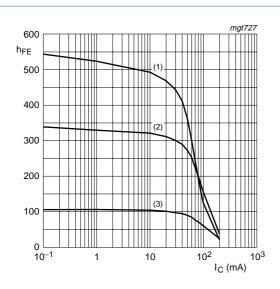
Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}$	-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	-	450	
V _{CEsat} collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	100	mV	
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[1] -	-	300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	-	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	580	655	700	mV
C _c	collector capacitance	$I_E = i_e = 0 A; V_{CB} = 10 V;$ f = 1 MHz	-	-	1.5	pF
C _e	emitter capacitance	$I_C = I_c = 0 \text{ A}; V_{EB} = 0.5 \text{ V};$ f = 1 MHz	-	11	-	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V};$ f = 100 MHz	100	-	-	MHz

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

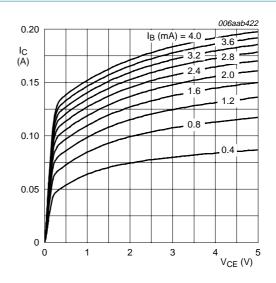
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$$V_{CE} = 5 V$$

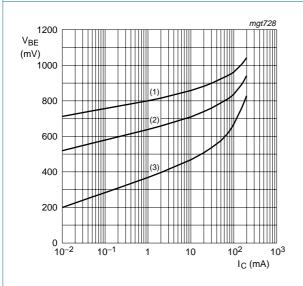
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = -55 \,^{\circ}C$

Fig 4. Per transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

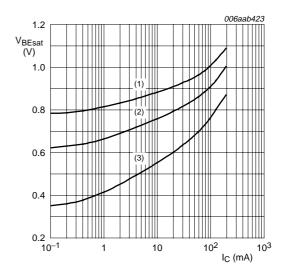
Fig 5. Per transistor: Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Per transistor: Base-emitter voltage as a function of collector current; typical values



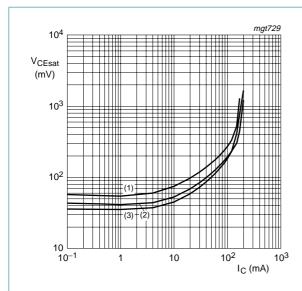
 $I_{\rm C}/I_{\rm B} = 20$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 7. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values

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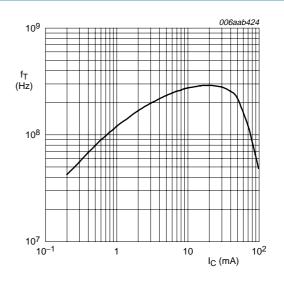
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$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values

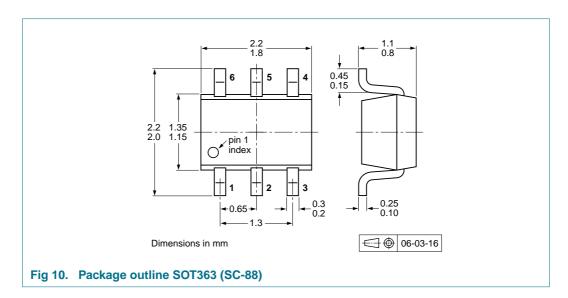


 V_{CE} = 5 V; f = 1 MHz; T_{amb} = 25 °C

Fig 9. Per transistor: Transition frequency as a function of collector current; typical values

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8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
BC847BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

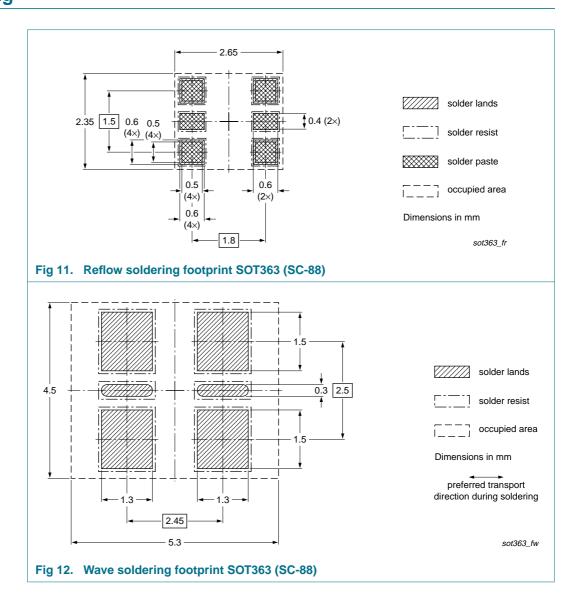
^[1] For further information and the availability of packing methods, see Section 13.

[2] T1: normal taping

[3] T2: reverse taping

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BC847BS_3	20090218	Product data sheet	-	BC847BS_2		
Modifications:	 The format of NXP Sem 		edesigned to comply wit	h the new identity guidelines		
	 Legal texts h 	nave been adapted to the ne	ew company name wher	e appropriate.		
	Section 4 "Marking": updated					
	Section 7 "Characteristics": enhanced					
	 Section 9 "Packing information": added 					
	 Section 10 " 	Soldering": added				
	Section 12 "	Legal information": updated				
BC847BS_2	19990428	Product specification	-	BC847BS_1		
BC847BS_1	19970714	Product specification	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BC847BS NXP Semiconductors

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